

## Panel Discussion

### Lithography for Future Submicron Device Fabrication

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Panelers: Joseph Borel (Thomson-EFCIS)  
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Toyoki Kitayama (Atsugi ECL, NTT)  
M.P. Lepselter (AT and T, Bell Lab.)  
Junji Matsui (Fundamental Res. Lab. Nippon Electric Co.)  
Makoto Nakase (VLSI Res. Center, Toshiba Co.)  
Jerome P. Silverman (IBM, Yorktown Heights)  
Organizer: Kenji Gamo (Osaka University)

Submicron lithography technique with a high throughput is crucial for future submicron device fabrication and many efforts have been done on various lithography techniques such as optical lithography, electron beam lithography, X-ray lithography and ion beam lithography. The present panel aims to discuss the state of the art and comparison with other techniques and the problems and promising solutions for future submicron devices or VLSI fabrication. Recent topics such as direct e-beam lithography and SOR X-ray lithography will also be discussed.

